



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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V_{DSS}	250V
$R_{DS(on)}$ (Max.)	235mΩ
I_D	12A
P_D	40W

●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.
- 5) Pb-free lead plating ; RoHS compliant
- 6) 100% Avalanche tested

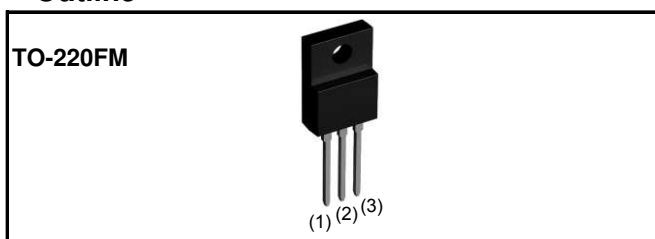
●Application

Switching Power Supply
 Automotive Motor Drive
 Automotive Solenoid Drive

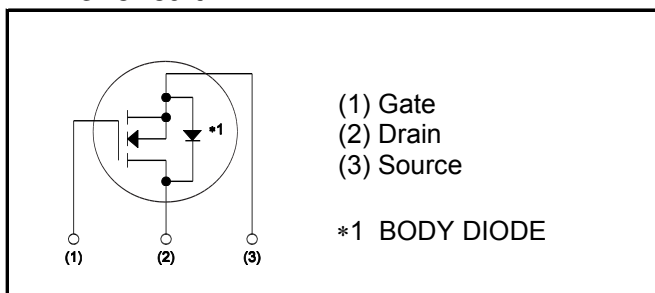
●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	250	V
Continuous drain current	$T_c = 25^\circ\text{C}$	I_D^{*1}	±12 A
	$T_c = 100^\circ\text{C}$	I_D^{*1}	±6.5 A
Pulsed drain current	$I_{D,pulse}^{*2}$	±48	A
Gate - Source voltage	V_{GSS}	±30	V
Avalanche energy, single pulse	E_{AS}^{*3}	10.5	mJ
Avalanche current	I_{AR}^{*3}	6.0	A
Power dissipation	$T_c = 25^\circ\text{C}$	P_D	40 W
	$T_a = 25^\circ\text{C}$	P_D	2.23 W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Bulk
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	RCX120N25

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	-	3.125	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	56	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	250	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 250V, V_{GS} = 0V$ $T_j = 25^\circ\text{C}$	-	-	10	μA
		$V_{DS} = 250V, V_{GS} = 0V$ $T_j = 125^\circ\text{C}$	-	-	100	
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	3.0	-	5.0	V
Static drain - source on - state resistance	$R_{DS(on)}^{*4}$	$V_{GS} = 10V, I_D = 6.0A$	-	180	235	$m\Omega$
		$V_{GS} = 10V, I_D = 6.0A$ $T_j = 125^\circ\text{C}$	-	340	480	
Forward transfer admittance	g_{fs}	$V_{DS} = 10V, I_D = 6.0A$	3.25	6.50	-	S

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C _{iss}	V _{GS} = 0V	-	1800	-	pF
Output capacitance	C _{oss}	V _{DS} = 25V	-	100	-	
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	60	-	
Turn - on delay time	t _{d(on)} ^{*4}	V _{DD} ≈ 125V, V _{GS} = 10V	-	33	-	ns
Rise time	t _r ^{*4}	I _D = 6.0A	-	65	-	
Turn - off delay time	t _{d(off)} ^{*4}	R _L = 20.83Ω	-	45	-	
Fall time	t _f ^{*4}	R _G = 10Ω	-	20	-	

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q _g ^{*4}	V _{DD} ≈ 125V	-	35	-	nC
Gate - Source charge	Q _{gs} ^{*4}	I _D = 12A	-	15	-	
Gate - Drain charge	Q _{gd} ^{*4}	V _{GS} = 10V	-	12	-	
Gate plateau voltage	V _(plateau)	V _{DD} ≈ 125V, I _D = 12A	-	7.6	-	V

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous source current	I _S ^{*1}	T _c = 25°C	-	-	12	A
Pulsed source current	I _{SM} ^{*2}		-	-	48	A
Forward voltage	V _{SD} ^{*4}	V _{GS} = 0V, I _S = 12A	-	-	1.5	V
Reverse recovery time	t _{rr} ^{*4}	I _S = 6.0A	-	105	-	ns
Reverse recovery charge	Q _{rr} ^{*4}	di/dt = 100A/μs	-	410	-	nC

*1 Limited only by maximum temperature allowed.

*2 P_w ≤ 10μs, Duty cycle ≤ 1%

*3 L ≈ 500μH, V_{DD} = 50V, R_G = 25Ω, starting T_j = 25°C

*4 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

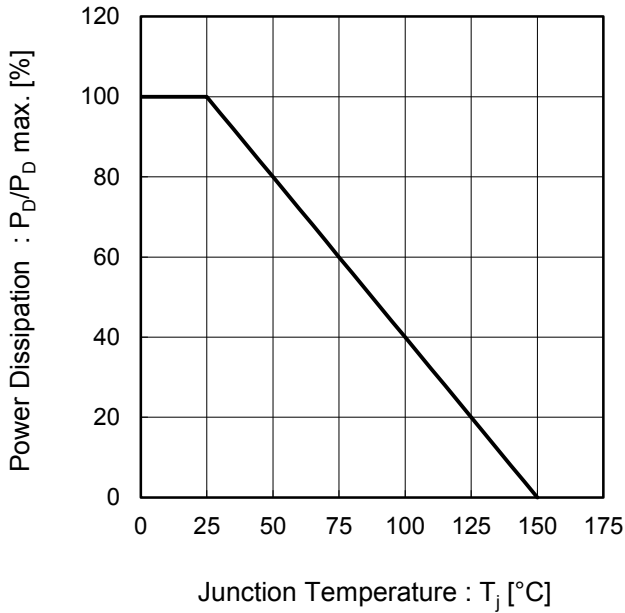


Fig.2 Maximum Safe Operating Area

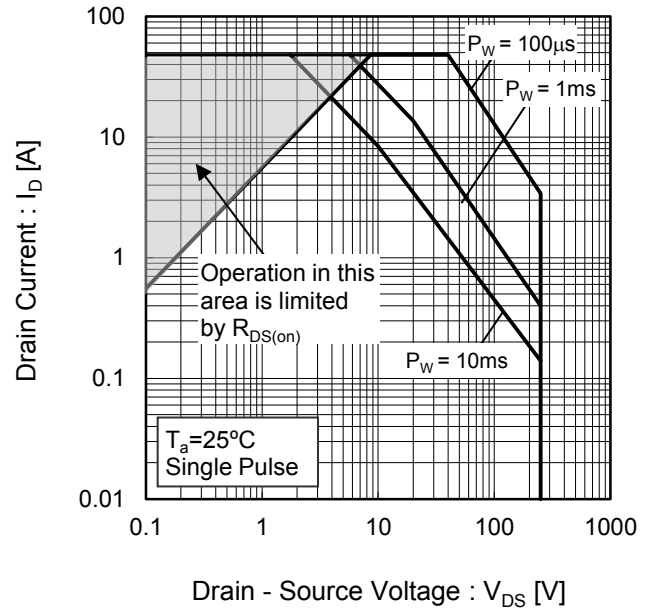
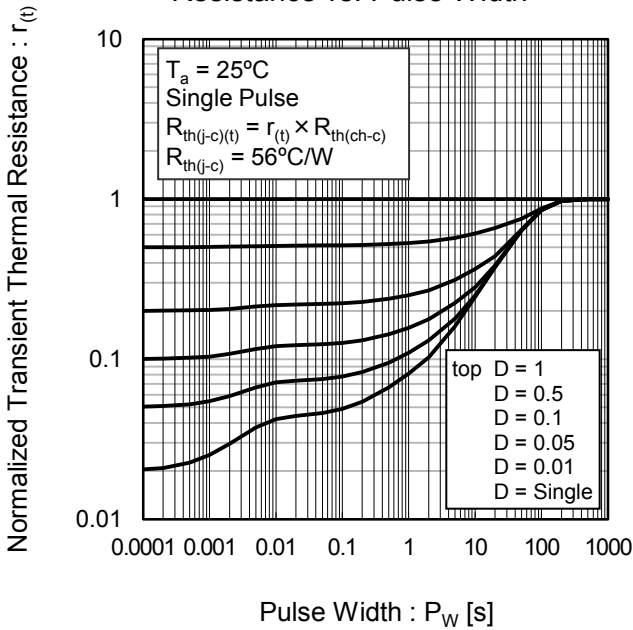


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Avalanche Current vs Inductive Load

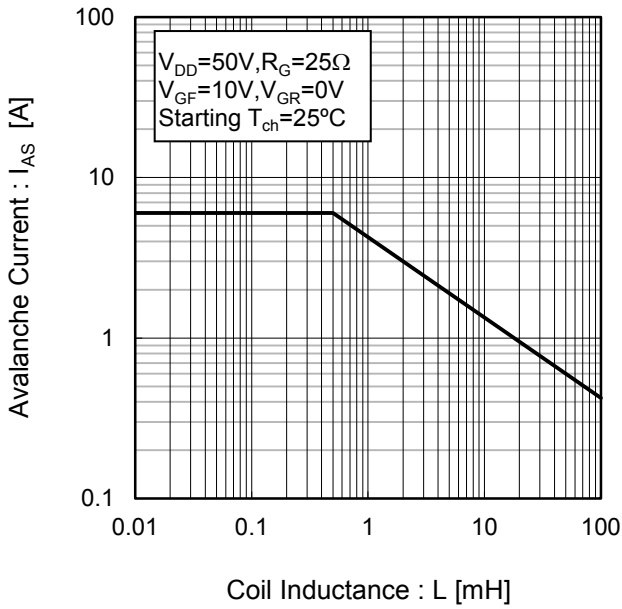


Fig.5 Avalanche Energy Derating Curve vs Junction Temperature

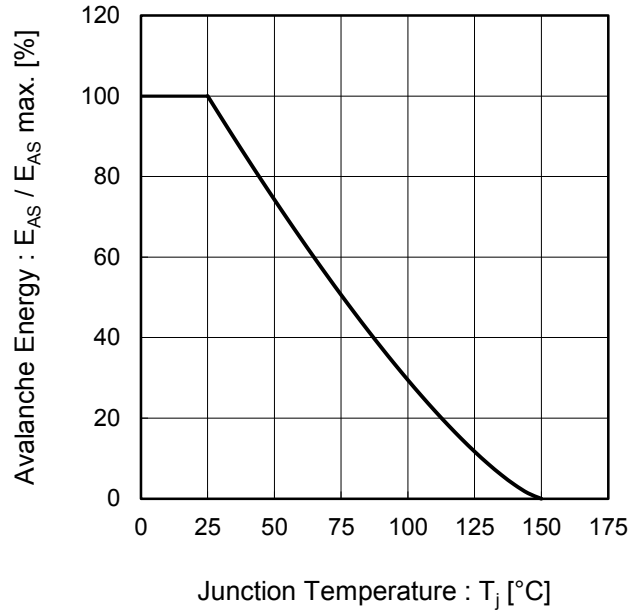


Fig.6 Typical Output Characteristics(I)

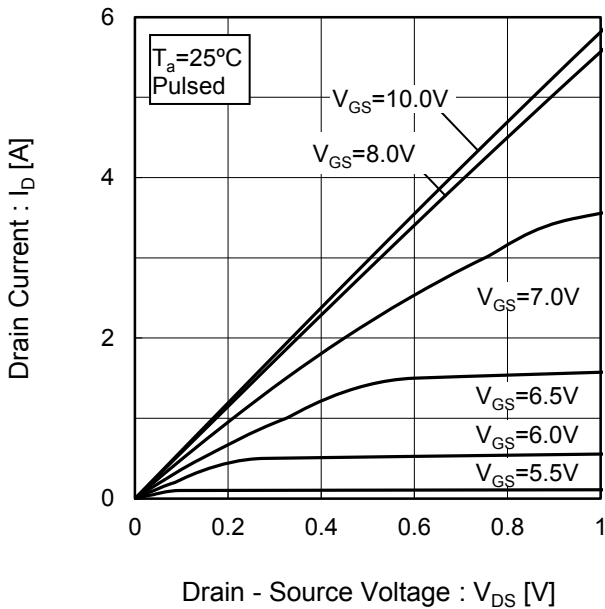
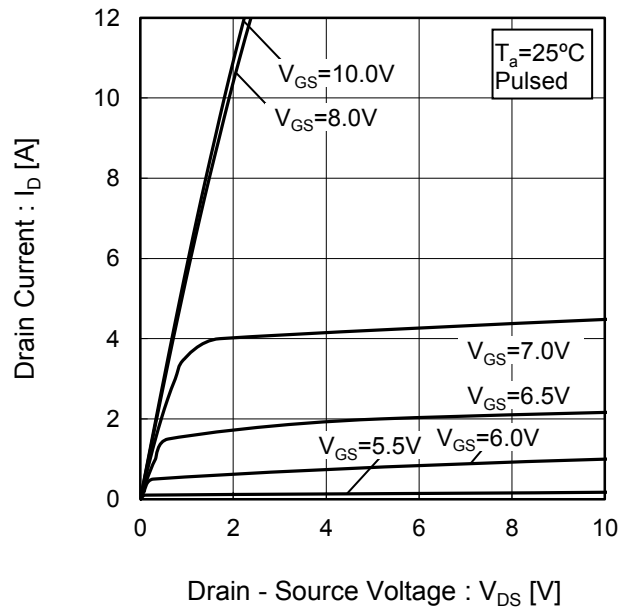


Fig.7 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Breakdown Voltage vs. Junction Temperature

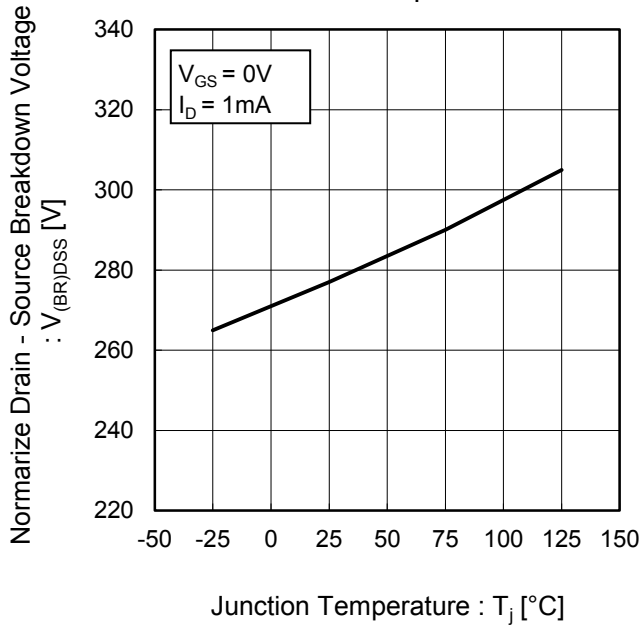


Fig.9 Typical Transfer Characteristics

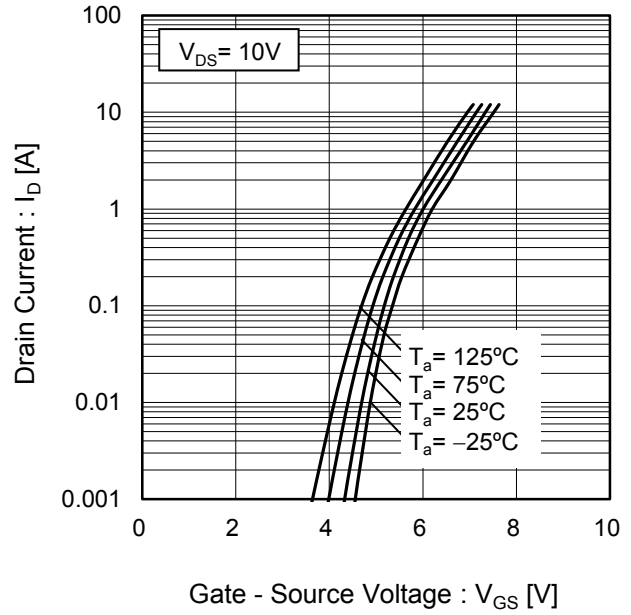


Fig.10 Gate Threshold Voltage vs. Junction Temperature

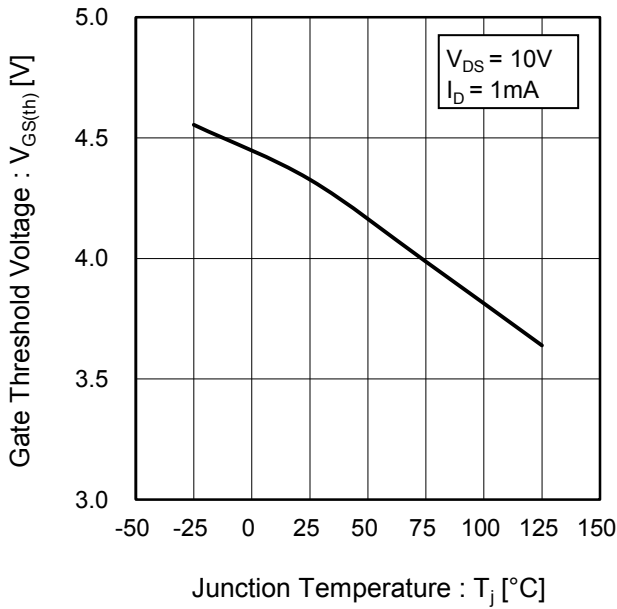
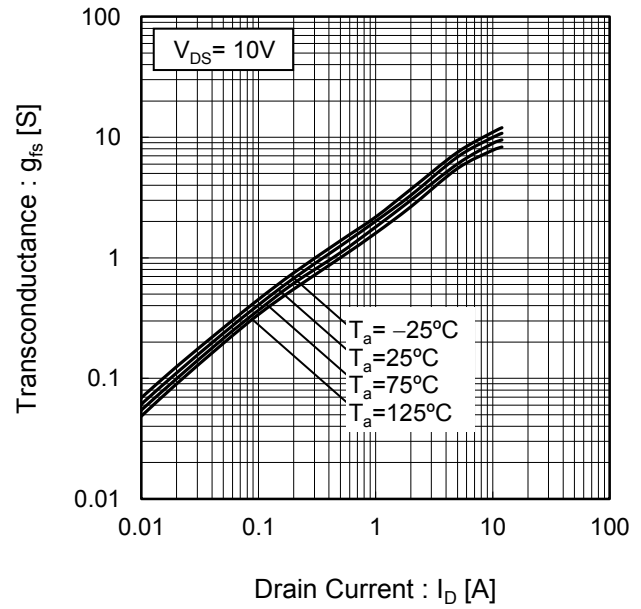


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

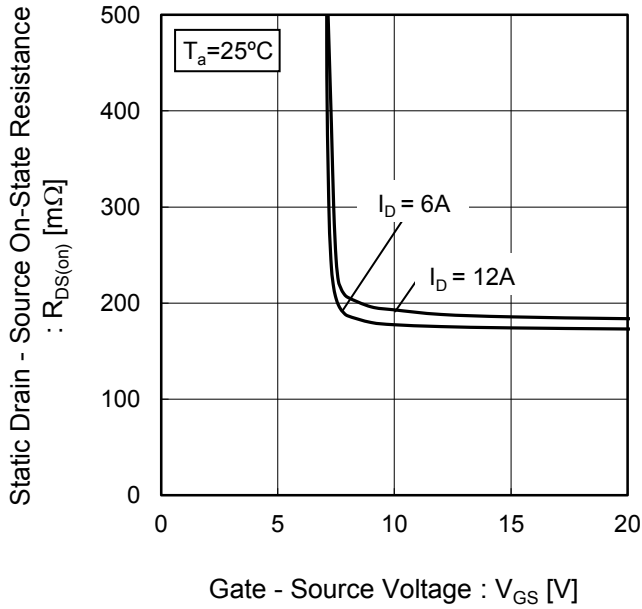


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

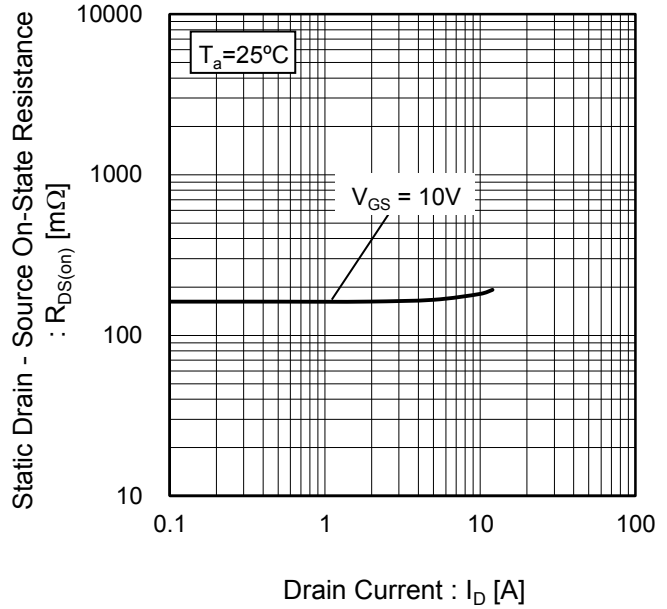
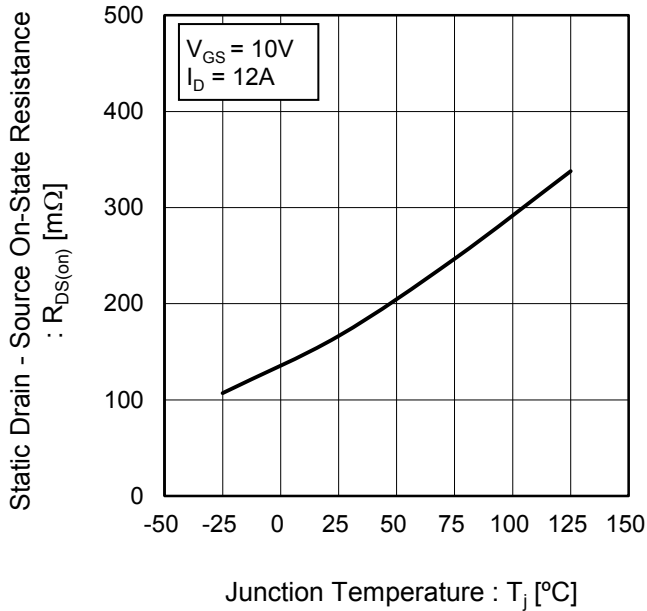


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(I)

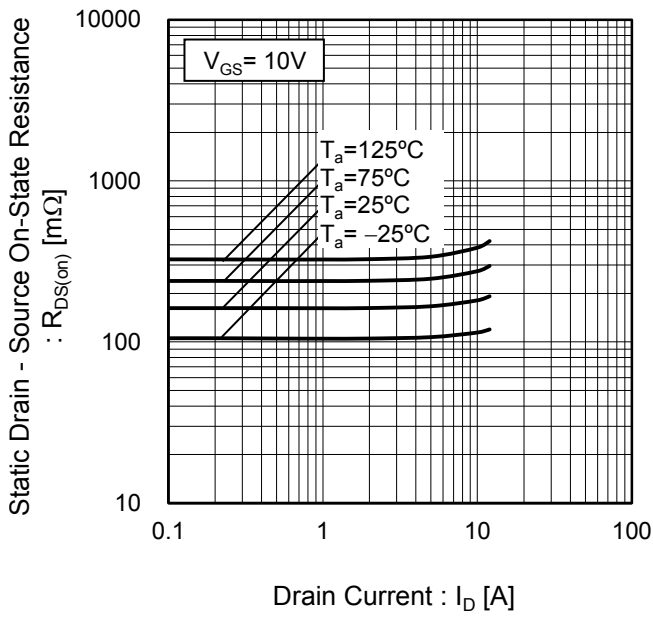
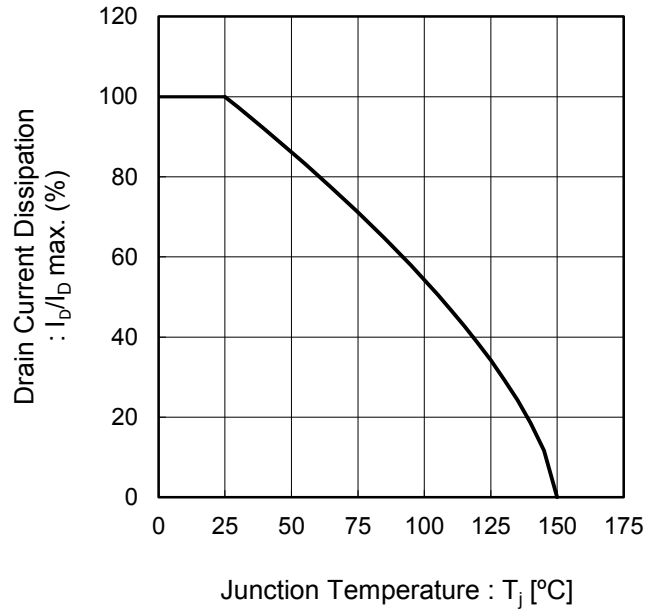


Fig.16 Drain Current Derating Curve



●Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

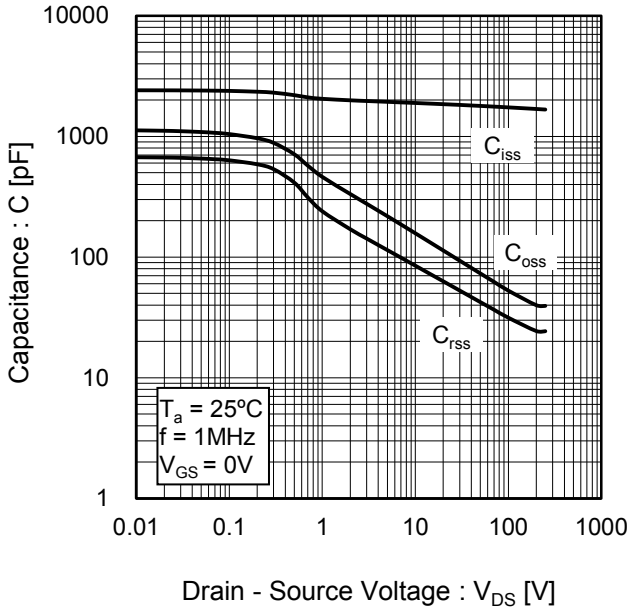


Fig.18 Switching Characteristics

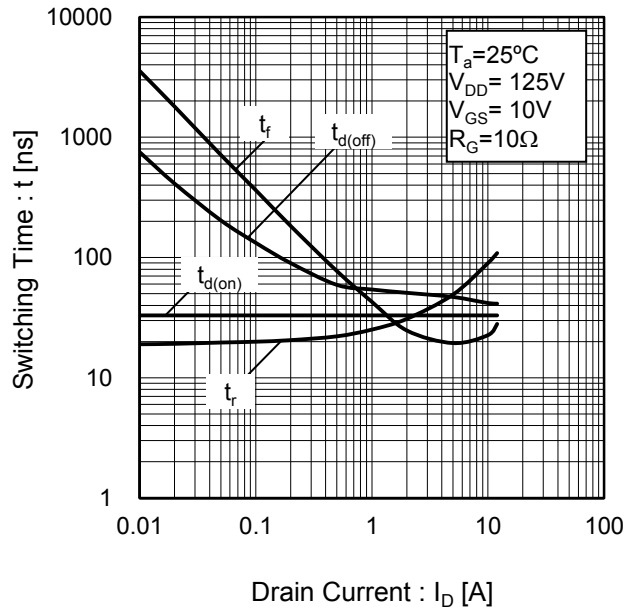
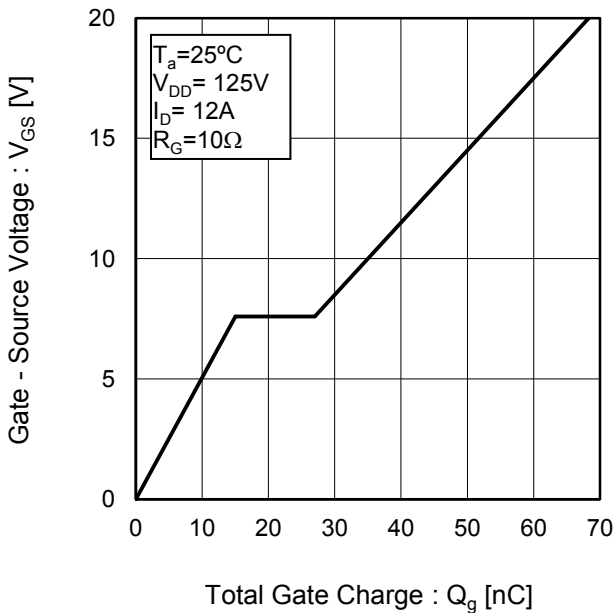


Fig.19 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.20 Source Current vs. Source - Drain Voltage

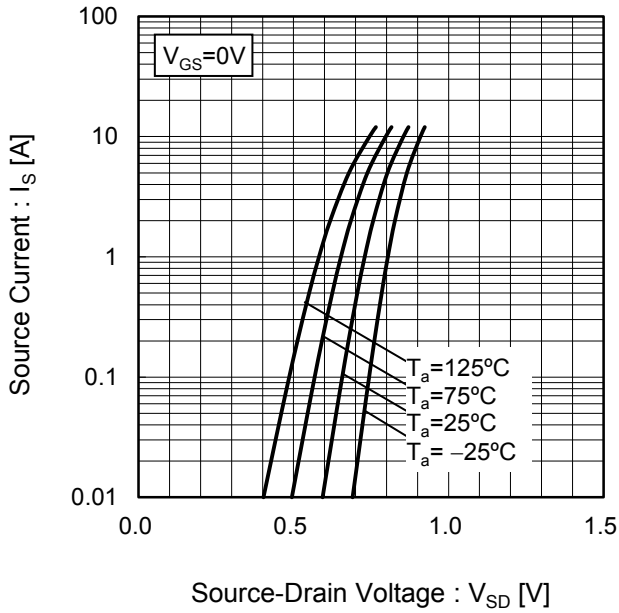
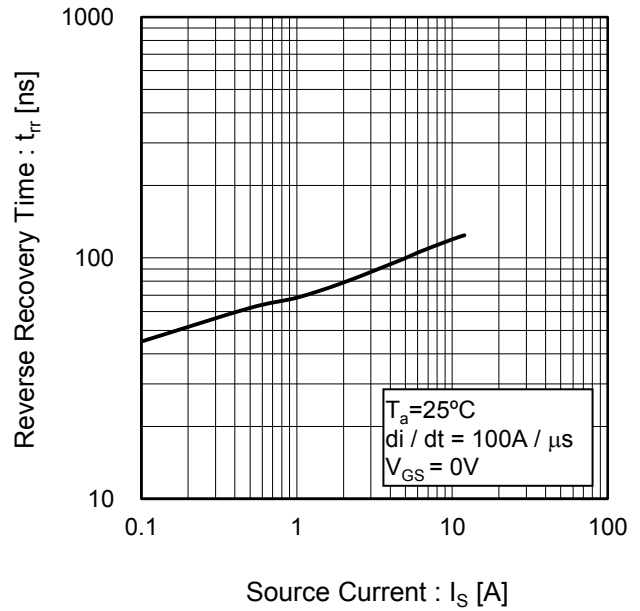


Fig.21 Reverse Recovery Time vs. Source Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

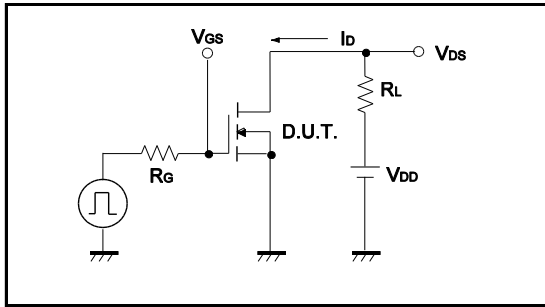


Fig.1-2 Switching Waveforms

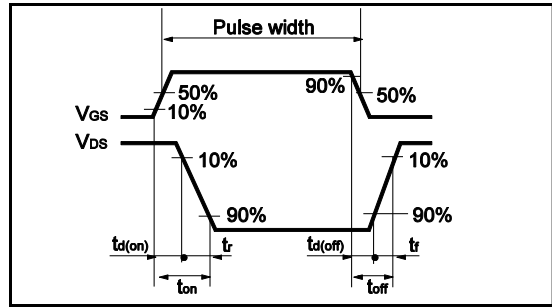


Fig.2-1 Gate Charge Measurement Circuit

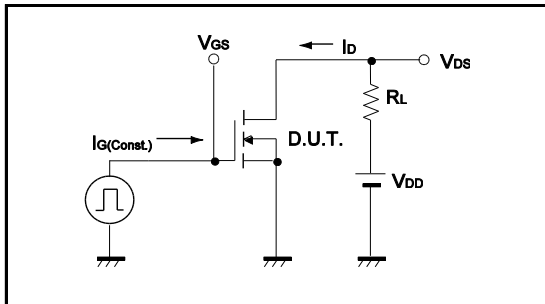


Fig.2-2 Gate Charge Waveform

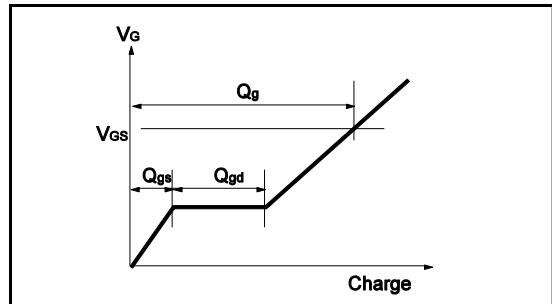


Fig.3-1 Avalanche Measurement Circuit

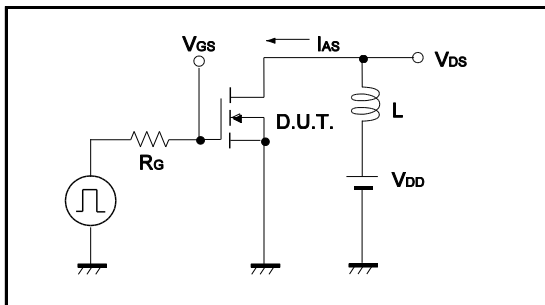
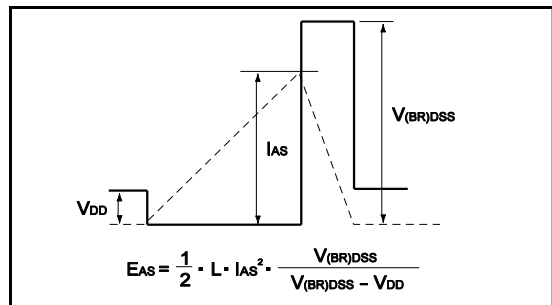
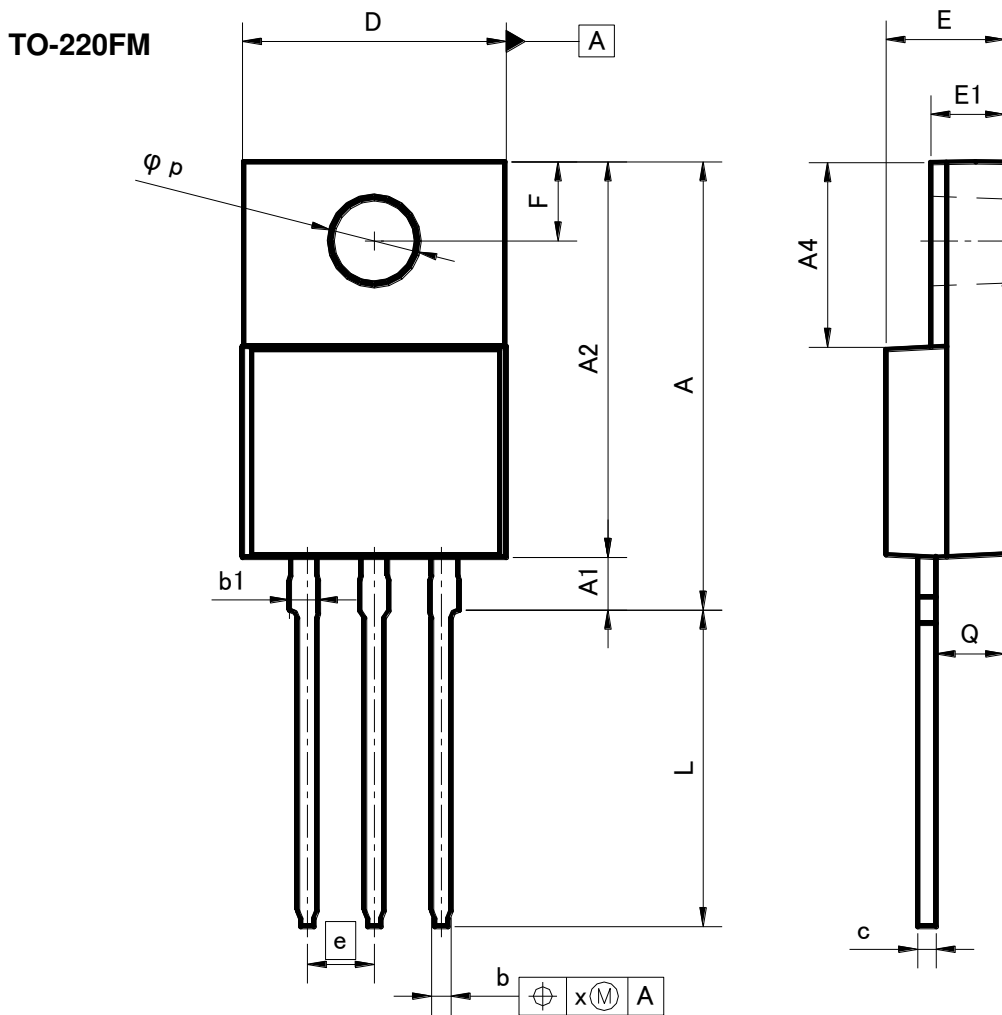


Fig.3-2 Avalanche Waveform



●Dimensions (Unit : mm)



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
c	0.70	0.85	0.028	0.033
D	9.90	10.30	0.39	0.406
E	4.40	4.80	0.173	0.189
e	2.54		0.10	
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.11	0.126
L	11.50	12.50	0.453	0.492
p	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
x	-	0.381	-	0.015

Dimension in mm/inches

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